

HVGT High voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

### SHAPE DISPLAY:



### FEATURES:

1. High reliability design.
2. High voltage design.
3. High frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

### APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. Other.

### MECHANICAL DATA:

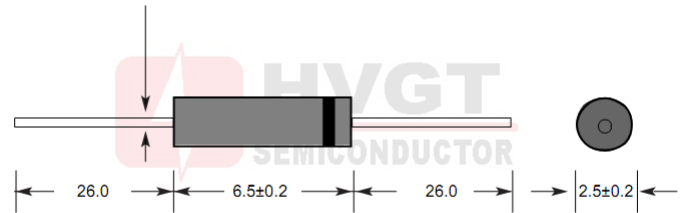
1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.18 grams (approx).

SIZE: (Unit:mm)

HVGT NAME: DO-206B

### DO-206B Series

Lead Diameter 0.6±0.03



Unit:mm

### MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_a=25^{\circ}C$ ;	6.0	kV
Average Output Current	$I_F$	$T_a=25^{\circ}C$ ;Resistive Load	5.0	mA
Suege Current	$I_{FSM}$	$T_a=25^{\circ}C$ ; 1/2 Sine(60Hz)	0.5	A
Junction Temperature	$T_J$		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	$T_C$		125	$^{\circ}C$
Storage Temperature	$T_{STG}$		-40~+125	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS: $T_a=25^{\circ}C$ (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	$V_F$	at $25^{\circ}C$ ; at $I_{F(AV)}$	20	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ ; at $V_{RRM}$	2.0	$\mu A$
	$I_{R2}$	at $100^{\circ}C$ ; at $V_{RRM}$	5.0	$\mu A$
Maximum Reverse Recovery Time	$T_{RR}$	at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$	80	nS
Junction Capacitance	$C_J$	at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$	2.0	pF



Fig1

Forward Characteristics

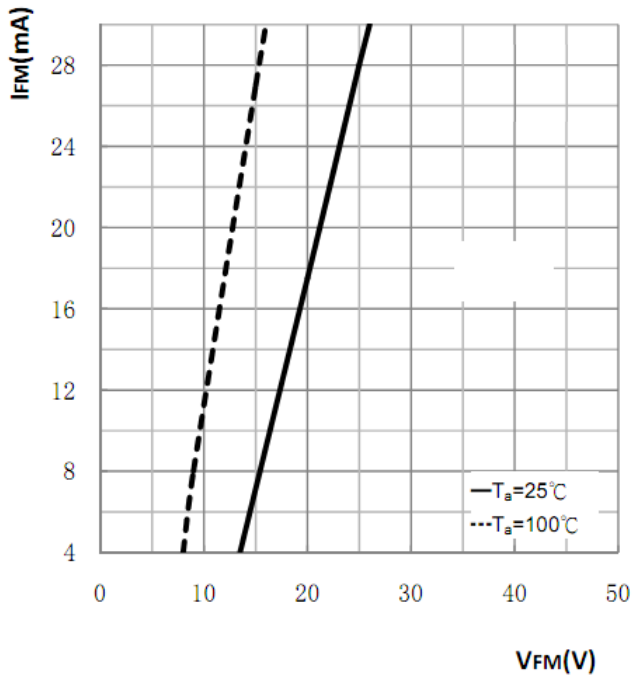


Fig2

Reverse Characteristics

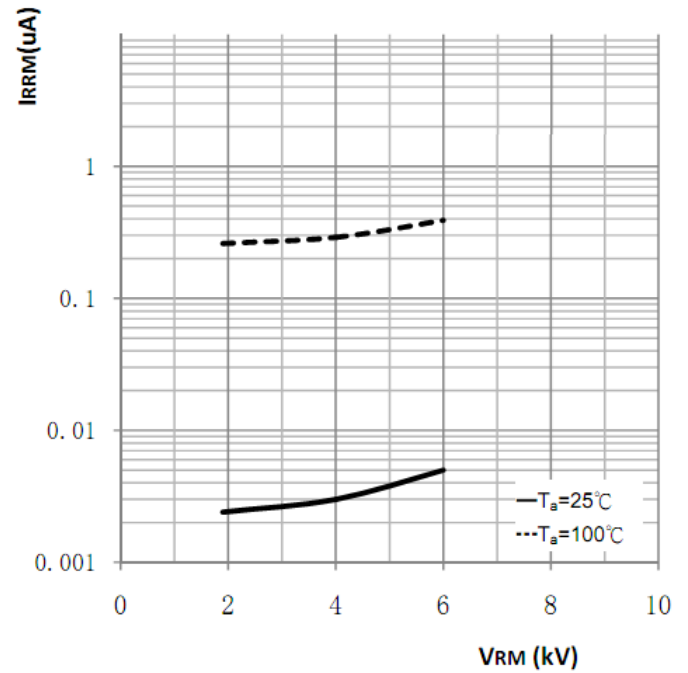


Fig3

VR-IF(AV) Curve

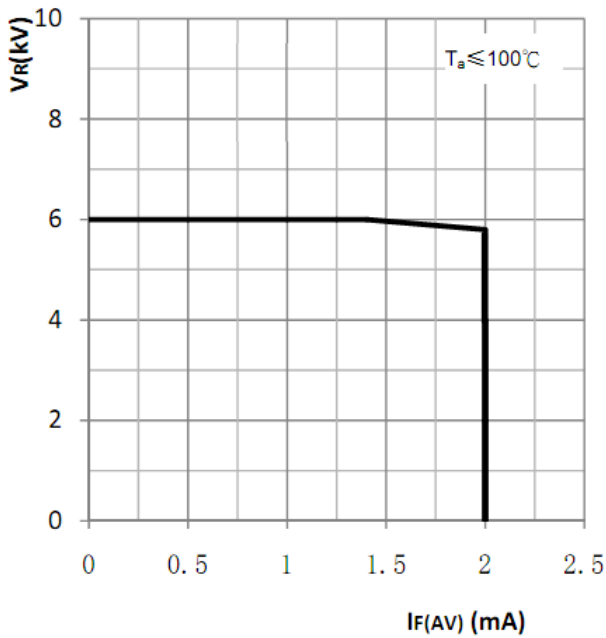
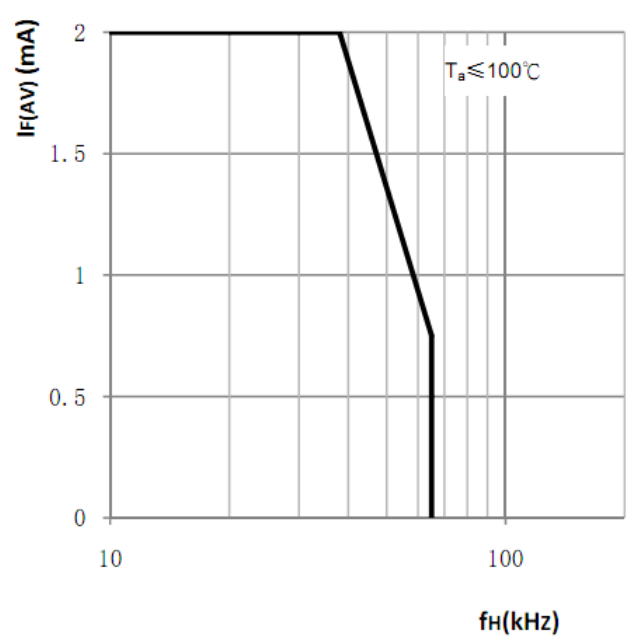


Fig4

IF(AV)-fH Curve



Marking

Type

ESJA08-06

Code

Cathode Mark

